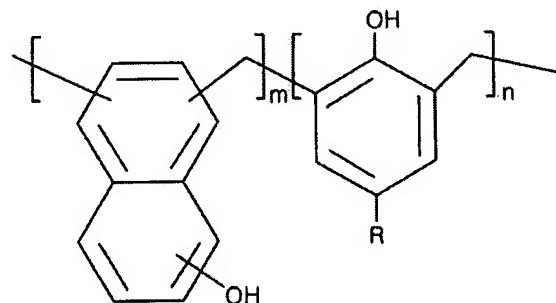


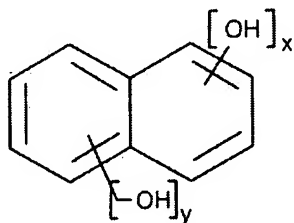
LISTING OF CLAIMS

1. (currently amended) A composition for a bottom-layer resist, comprising a polymer represented by the following formula:



wherein R is hydrogen or a methyl group, $m/(m+n)$ is about 0.5 to about 1.0 and $n/(m+n)$ is 0 to about 0.5; and
a thermal acid generator (TAG).

2. (original) The composition as claimed in claim 1, further comprising a cross-linker represented by the following formula:



wherein x is an integer in the range of 1 to 3, and y is an integer in the range of 2 to 4.

3. (original) The composition as claimed in claim 2, wherein the cross-linker comprises about 10 to about 40 wt.% based upon the total weight of the polymer.

4. (currently amended) The composition as claimed in claim 1, ~~further comprising a thermal acid generator (TAG),~~ wherein the TAG is about 1 to about 15 wt. % based on the total weight of the polymer.

5. (currently amended) The composition as claimed in claim 4, wherein the TAG is a

compound selected from a group consisting of aromatic sulfonic acid salts.

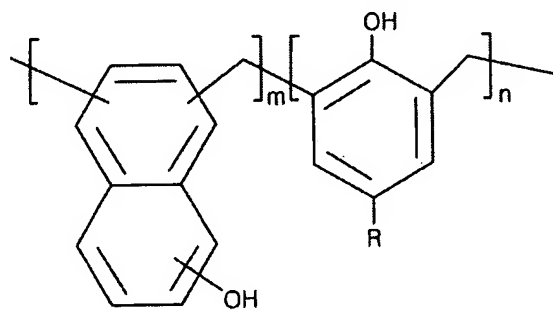
6. (original) The composition as claimed in claim 4, wherein the TAG is ammonium toluene sulfonate.

7. (canceled)

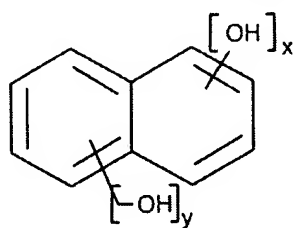
8. (canceled)

9. (original) A patterning method for a semiconductor device comprising:

(a) forming a first resist layer by coating a resist composition on a layer to be etched on a semiconductor substrate, wherein the resist composition is represented by the following formula:



wherein R is hydrogen or a methyl group, $m/(m+n)$ is about 0.5 to about 1.0 and $n/(m+n)$ is 0 to about 0.5, and wherein the resist composition further includes a temperature acid generator (TAG), and a crosslinker agent represented by the following



wherein x is an integer in the range of 1 to 3, and y is an integer in the range of 2 to 4;

(b) baking the first resist layer, thereby forming a bottom resist layer;

(c) forming a second resist layer containing silicon on the bottom resist layer;

(d) pre-baking the second resist layer;

(e) exposing the second resist layer to light;

- (f) performing a post-exposure baking (PEB) on the second resist layer;
- (g) forming a top layer resist pattern by developing the exposed second resist layer;
- (h) forming a bottom resist layer pattern by etching the bottom resist layer using the top layer resist pattern as an etching mask; and
- (i) etching the layer to be etched using the bottom resist layer pattern as an etching mask.

10. (original) The patterning method of claim 9, wherein in step (e), ArF or F₂ eximer laser is used for the exposing.

11. (currently amended) The patterning method of claim 9, wherein the TAG is a compound selected from a group consisting of aromatic sulfonic acid salts.

12. (original) The patterning method of claim 9, wherein the TAG is ammonium toluene sulfonate.